## Maxime Berthe

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/4271904/publications.pdf

Version: 2024-02-01

24 papers 865

16 h-index 642732 23 g-index

24 all docs

24 docs citations

times ranked

24

1556 citing authors

#	Article	IF	CITATIONS
1	Transport Properties of Methyl-Terminated Germanane Microcrystallites. Nanomaterials, 2022, 12, 1128.	4.1	1
2	Engineering a Robust Flat Band in III–V Semiconductor Heterostructures. Nano Letters, 2021, 21, 680-685.	9.1	19
3	Three dimensional resistance mapping of self-organized Sr3V2O8 nanorods on metallic perovskite SrVO3 matrix. Applied Surface Science, 2020, 510, 145522.	6.1	14
4	Importance of point defect reactions for the atomic-scale roughness of Ill–V nanowire sidewalls. Nanotechnology, 2019, 30, 324002.	2.6	5
5	Resolving the Controversial Existence of Silicene and Germanene Nanosheets Grown on Graphite. ACS Nano, 2018, 12, 4754-4760.	14.6	35
6	Shallow Heavily Doped n++ Germanium by Organo-Antimony Monolayer Doping. ACS Applied Materials & Samp; Interfaces, 2017, 9, 20179-20187.	8.0	17
7	Scanning tunnelling spectroscopy and Raman spectroscopy of monolayer silicene on Ag(111). Surface Science, 2016, 653, 92-96.	1.9	17
8	Type I band alignment in GaAs81Sb19/GaAs core-shell nanowires. Applied Physics Letters, 2015, 107, .	3.3	14
9	Functionalization of Silica Nanoparticles and Native Silicon Oxide with Tailored Boron-Molecular Precursors for Efficient and Predictive <i>p</i> -Doping of Silicon. Journal of Physical Chemistry C, 2015, 119, 13750-13757.	3.1	25
10	High charge mobility in two-dimensional percolative networks of PbSe quantum dots connected by atomic bonds. Nature Communications, 2015, 6, 8195.	12.8	125
11	Nonstoichiometric Low-Temperature Grown GaAs Nanowires. Nano Letters, 2015, 15, 6440-6445.	9.1	9
12	Nanoscale Carrier Multiplication Mapping in a Si Diode. Nano Letters, 2014, 14, 5636-5640.	9.1	5
13	Synthesis and electrical conductivity of multilayer silicene. Applied Physics Letters, 2014, 104, .	3.3	136
14	Persistent enhancement of the carrier density in electron irradiated InAs nanowires. Nanotechnology, 2013, 24, 275706.	2.6	25
15	Band offsets at zincblende-wurtzite GaAs nanowire sidewall surfaces. Applied Physics Letters, 2013, 103, .	3.3	28
16	Faceting, composition and crystal phase evolution in III–V antimonide nanowire heterostructures revealed by combining microscopy techniques. Nanotechnology, 2012, 23, 095702.	2.6	95
17	Investigation of the negative differential resistance reproducibility in AlN/GaN double-barrier resonant tunnelling diodes. Applied Physics Letters, 2011, 99, 182109.	3.3	34
18	Coulomb Energy Determination of a Single Si Dangling Bond. Physical Review Letters, 2010, 105, 226404.	7.8	34

#	ARTICLE	IF	CITATION
19	Faceted sidewalls of silicon nanowires: Au-induced structural reconstructions and electronic properties. Physical Review B, 2010, 81, .	3.2	47
20	Probing the Carrier Capture Rate of a Single Quantum Level. Science, 2008, 319, 436-438.	12.6	60
21	Reversible Defect Engineering of Single-Walled Carbon Nanotubes Using Scanning Tunneling Microscopy. Nano Letters, 2007, 7, 3623-3627.	9.1	46
22	Anisotropic Free-Electron-Like Dispersions and Standing Waves Realized in Self-Assembled Monolayers of Glycine on Cu(100). Journal of the American Chemical Society, 2007, 129, 740-741.	13.7	23
23	Electron Transport via Local Polarons at Interface Atoms. Physical Review Letters, 2006, 97, 206801.	7.8	50
24	Assessing the insulating properties of an ultrathin SrTiO3 shell grown around GaAs nanowires with molecular beam epitaxy. Nanotechnology, $0$ , , .	2.6	1